Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.50$ V at $I_F = 5$ A

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

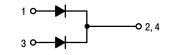
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

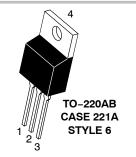


ON Semiconductor®

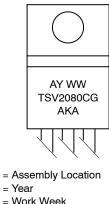
www.onsemi.com

PIN CONNECTIONS





MARKING DIAGRAMS



WW = Work Week

А

Y

- AKA = Polarity Designator
- G = Pb-Free Package/Halide Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	80	V
Average Rectified Forward Current (Rated V_R , T_C = 130°C)	Per device Per diode	I _{F(AV)}	20 10	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 125°C)	Per device Per diode	I _{FRM}	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	100	A
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

	Rating Symbol Value		Value	Unit
Maximum Thermal Resistance	Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.0 70	°C/W °C/W

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

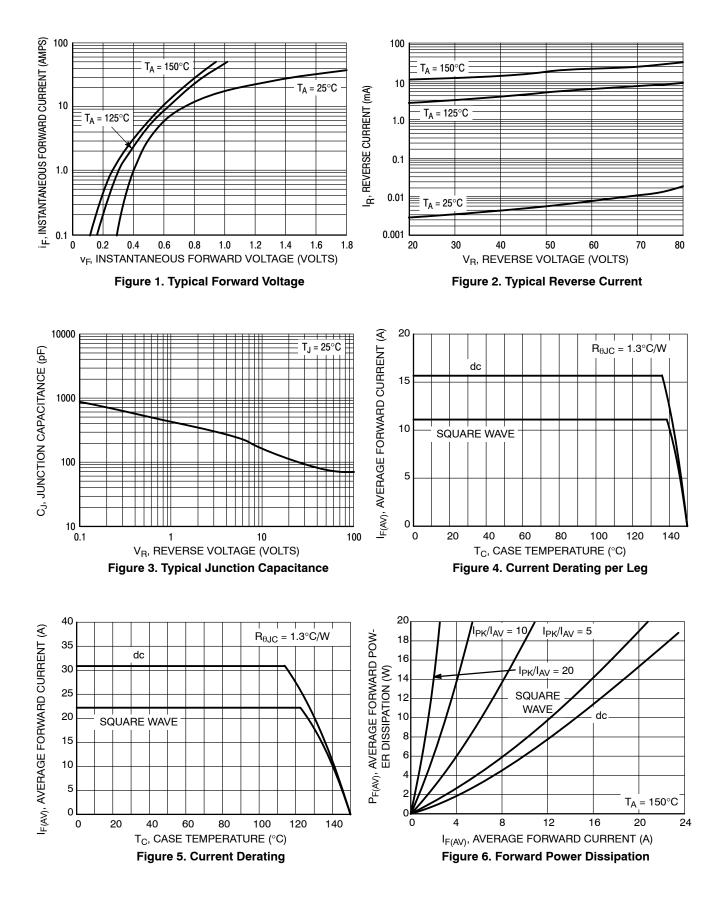
Rating	Symbol	Тур	Мах	Unit
Maximum Instantaneous Forward Voltage (Note 1) $(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$ $(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$	VF	0.55 0.65	_ 0.98	V
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$		0.50 0.58	_ 0.82	
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)	I _R	20 10	600 20	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\le 2.0\%$

ORDERING INFORMATION

Device	Package	Shipping
NTSV2080CTG	TO-220AB (Pb-Free/Halide Free)	50 Units / Rail

TYPICAL CHARACTERISITICS



TYPICAL CHARACTERISITICS

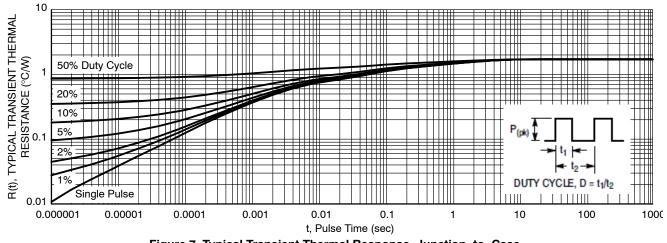


Figure 7. Typical Transient Thermal Response, Junction-to-Case

PACKAGE DIMENSIONS

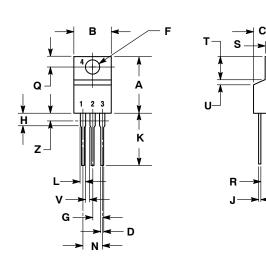
TO-220 CASE 221A-09 ISSUE AH

-T- SEATING PLANE



 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 CONTROLLING DIMENSION: INCH.
DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.



	INCHES		MILLIN	NILLIMETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Η	0.110	0.161	2.80	4.10	
ſ	0.014	0.024	0.36	0.61	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Ζ		0.080		2.04	

STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

ON Semiconductor and the intervent and the inter

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative